

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	13mΩ@10V	18A
	16mΩ@4.5V	

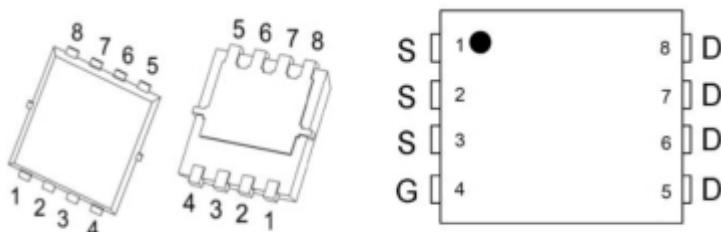
Feature

- Fast switching speed
- Surface mount package
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

Applications

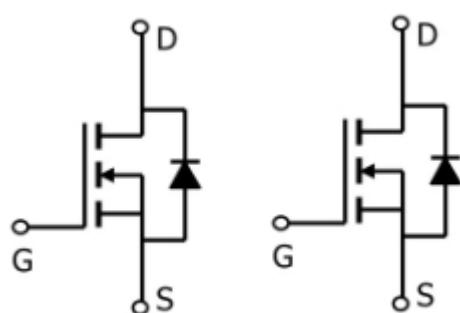
- DC-DC Converters.
- Motor Control.

Package



PDFNWB3.3×3.3-8L

Circuit diagram



Marking



60N13GD =Device Code
* =Month Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current($T_c=25^\circ\text{C}$)	I_D	18	A
Pulse Drain Current Tested	I_{DM}	72	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	50	W
Thermal Resistance-Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Maximum Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature Range	T_{STG} ,	-55 to 150	$^\circ\text{C}$



ZL MOSFET

ZL60N13GDA

Electrical characteristics

(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		13	16	mΩ
		V _{GS} = 4.5V, I _D = 10A		16	21	
Dynamic and Switching Characteristics						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =30V, f=1MHz		426		pF
Output capacitance	C _{oss}			103		
Reverse transfer capacitance	C _{rss}			8		
Turn-on Delay Time	T _{d(on)}	V _{DD} =30V, I _D = 10A, V _{GS} =10V, R _G = 1.6Ω		8		nS
Turn-on Rise Time	T _r			5		
Turn-Off Delay Time	T _{d(off)}			24		
Turn-Off Fall Time	t _f			3.5		
Total Gate Charge	Q _g	V _{DS} =30V , V _{GS} =10V, I _D = 10A		35		pF
Gate-Source Charge	Q _{gs}			6.4		
Gate-Drain Charge	Q _{gd}			3.5		
Drain-Source Body Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =1A			1.2	V

Typical Characteristics

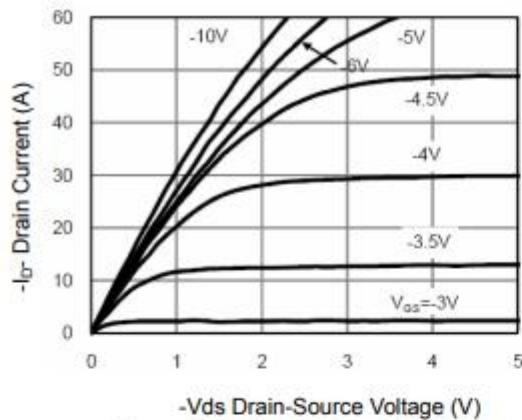


Figure 1 Output Characteristics

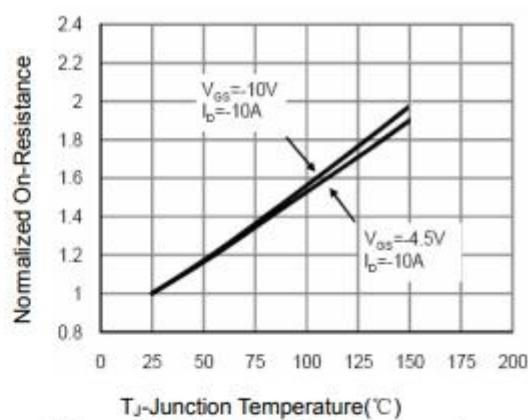


Figure 4 Rdson-JunctionTemperature

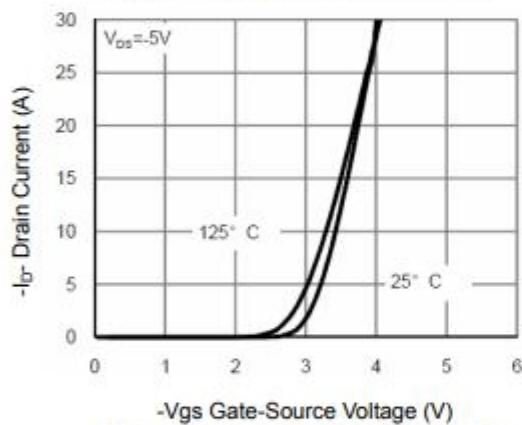


Figure 2 Transfer Characteristics

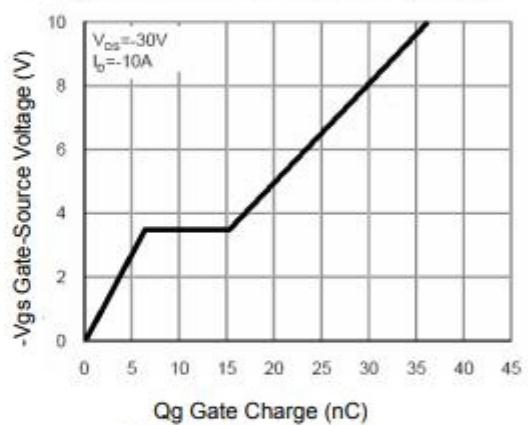


Figure 5 Gate Charge

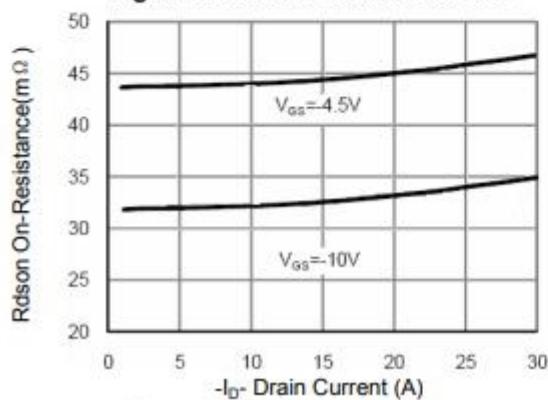


Figure 3 Rdson- Drain Current

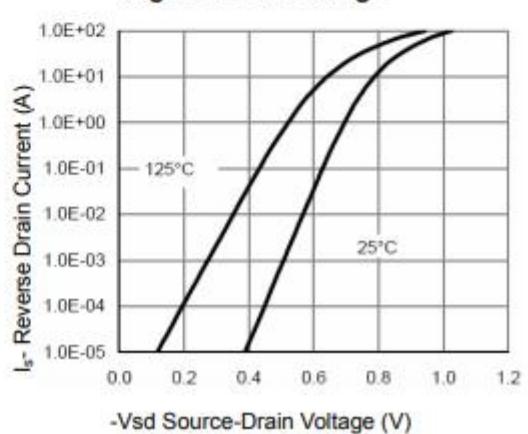


Figure 6 Source- Drain Diode Forward

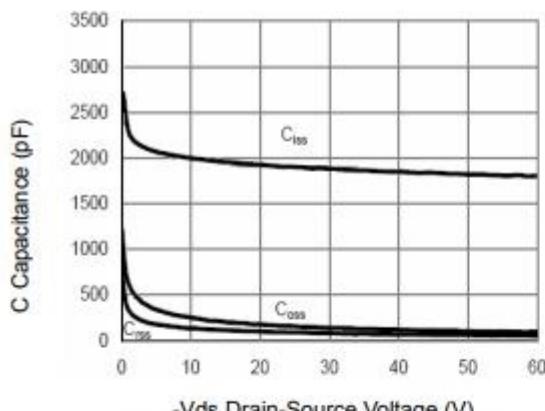


Figure 7 Capacitance vs Vds

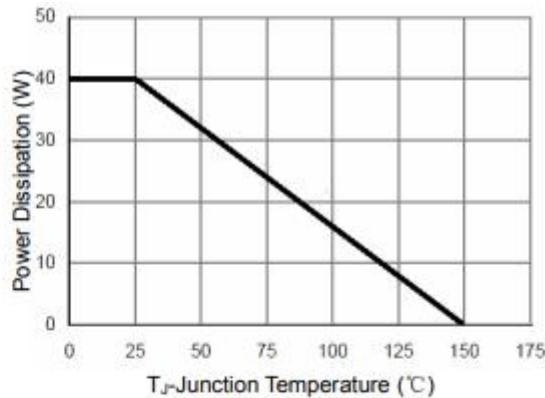


Figure 9 Power De-rating

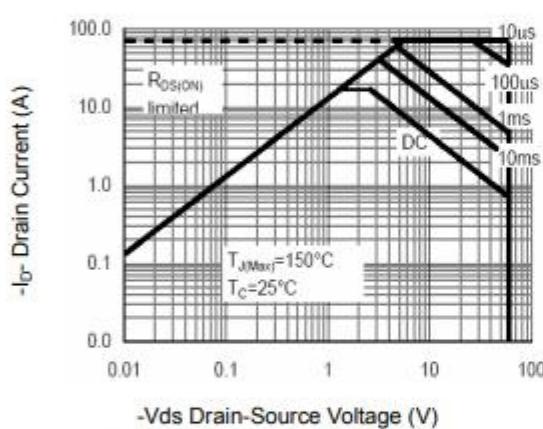


Figure 8 Safe Operation Area

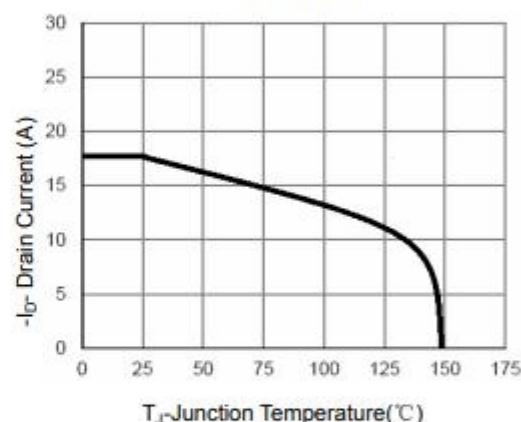


Figure 10 ID Current De-rating

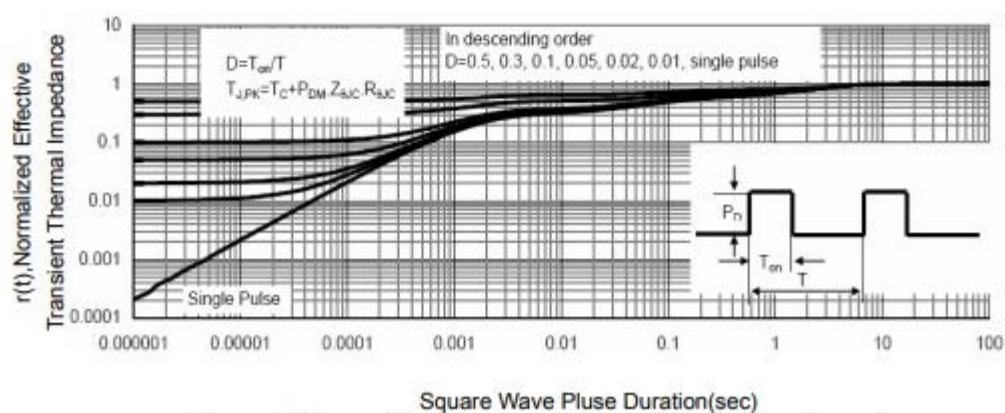
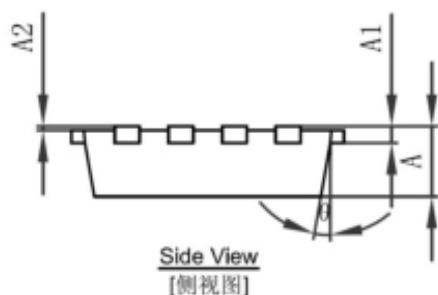
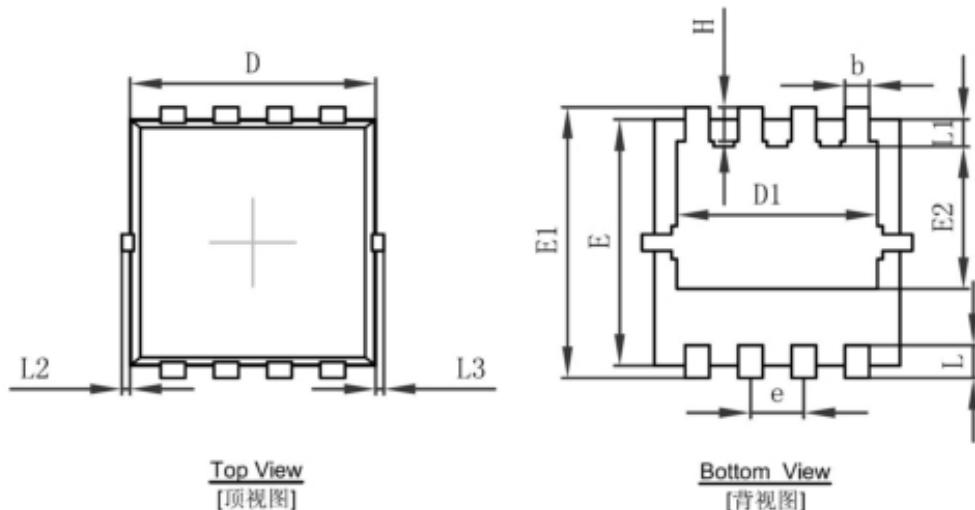


Figure 11 Normalized Maximum Transient Thermal Impedance

PDFNWB3.3×3.3-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°		13°	